

IGBT MODULE (N series)

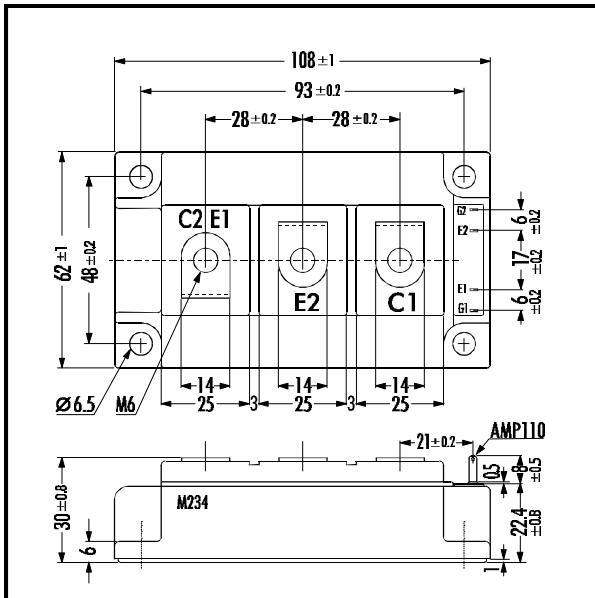
■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Improved FWD Characteristic
- Minimized Internal Stray Inductance
- Overcurrent Limiting Function (4~5 Times Rated Current)

■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

■ Outline Drawing



■ Maximum Ratings and Characteristics

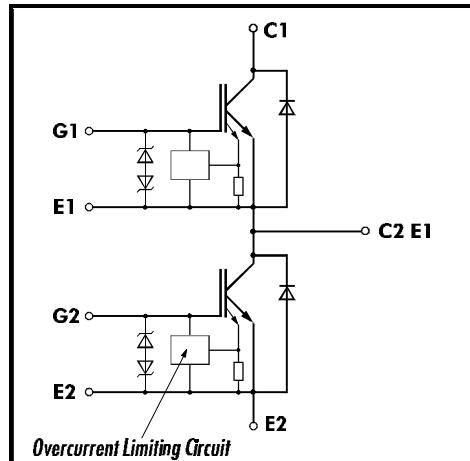
• Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	1200	V
Gate -Emitter Voltage	V_{GES}	± 20	V
Collector Current	Continuous I_C	200	A
	1ms $I_{C PULSE}$	400	
	Continuous $-I_C$	200	
	1ms $-I_{C PULSE}$	400	
Max. Power Dissipation	P_C	1500	W
Operating Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +125	$^\circ\text{C}$
Isolation Voltage	A.C. 1min. V_{is}	2500	V
Screw Torque	Mounting *1	3.5	Nm
	Terminals *2	4.5	

Note: *1: Recommendable Value; 2.5 ~ 3.5 Nm (M5) or (M6)

*2: Recommendable Value; 3.5 ~ 4.5 Nm (M6)

■ Equivalent Circuit



• Electrical Characteristics (at $T_j=25^\circ\text{C}$)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0\text{V}$ $V_{CE}=1200\text{V}$			2.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0\text{V}$ $V_{GE}=\pm 20\text{V}$			30	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=20\text{V}$ $I_C=200\text{mA}$	4.5		7.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V}$ $I_C=200\text{A}$			3.3	V
Input capacitance	C_{ies}	$V_{GE}=0\text{V}$	32000			pF
	C_{ges}	$V_{CE}=10\text{V}$	11600			
	C_{res}	$f=1\text{MHz}$	10320			
Turn-on Time	t_{ON}	$V_{CC}=600\text{V}$	0.65	1.2		μs
	t_r	$I_C=200\text{A}$	0.25	0.6		
Turn-off Time	t_{OFF}	$V_{GE}=\pm 15\text{V}$	0.85	1.5		
	t_f	$R_G=4.7\Omega$	0.35	0.5		
Diode Forward On-Voltage	V_F	$I_F=200\text{A}$ $V_{GE}=0\text{V}$			3.0	V
Reverse Recovery Time	t_{rr}	$I_F=200\text{A}$			350	ns

• Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.085	$^\circ\text{C/W}$
	$R_{th(j-c)}$	Diode			0.22	
	$R_{th(c-f)}$	With Thermal Compound		0.025		